

*SPECIFICATION AMENDMENTS*

Replace the paragraph beginning at page 13, line 15 with:

Fig. 10 is a cross-sectional view taken along line ~~A-A'~~ X-X of Fig. 9;

Replace the paragraph beginning at page 13, line 18 with:

Fig. 12 is a cross-sectional view taken along line ~~A-A'~~ XII-XII of the MOS transistor shown in Fig. 11;

Replace the paragraph beginning at page 13, line 20 with:

Fig. 13 is a cross-sectional view taken along line ~~B-B'~~ XIII-XIII of the MOS transistor shown in Fig. 11;

Replace the paragraph beginning at page 26, line 15 with:

Fig. 9 is a top pattern diagram illustrating the configuration of a MOS transistor according to a fifth embodiment of the present invention. Fig. 10 is a cross-sectional view taken along line ~~A-A'~~ X-X shown in Fig. 9. The fifth embodiment explains still another configuration example of the MOS transistor in which the control gates are provided located on both the opposite sides of the main gate, in the gate lengthwise direction of the gate, namely, on the ~~sides of the~~ source area and the drain area sides in the MOS transistor shown in Fig. 1B.

Replace the paragraph beginning at page 28, line 16 with:

Figs. 11 to 13 are pattern diagrams illustrating the configuration of a MOS transistor according to a sixth embodiment of the present invention. Fig. 11 is a top view. Fig. 12 is a cross-sectional view taken along line ~~A-A'~~ XII-XII of Fig. 11. Fig. 13 is a cross-sectional view taken along line ~~B-B'~~ XIII-XIII of Fig. 11.